



INTERNATIONAL ATOMIC ENERGY AGENCY
UNITED NATIONS EDUCATIONAL, SCIENTIFIC AND CULTURAL ORGANIZATION



INTERNATIONAL CENTRE FOR THEORETICAL PHYSICS

34100 TRIESTE (ITALY) - P.O.B. 588 - MIRAMARE - STRADA COSTIERA 11 - TELEPHONE: 2240-1
CABLE: CENTRATON - TELEX 460392 - I

SMR/384 - 7

**EXPERIMENTAL WORKSHOP ON
"HIGH TEMPERATURE SUPERCONDUCTORS"
(30 March - 14 April 1989)**

**PHENOMENOLOGY AND THEORY OF SUPERCONDUCTIVITY
(Lecture IV)**

Narendra KUMAR
Department of Physics
Indian Institute of Science
560 012 Bangalore
India

These are preliminary lecture notes, intended only for distribution to participants.

INTRODUCTION to HTSC of Lecture I)

* $\text{La}_{2-x}(\text{Ba}, \text{Sr})_x\text{CuO}_{4-y}$, $T_c \sim 40\text{K}$ ($x \sim 0.15$, $y \sim 0$)

$T_c(\text{Hg}) \sim 4\text{K}$

* $\text{YBa}_2\text{Cu}_3\text{O}_{7-\delta}$, $T_c \sim 90\text{K}$ ($\delta \sim 0$)

compare: $T_c(\text{Nb}_3\text{Ge}) \sim 23.2\text{K}$

$\text{LHe} \sim 4.2\text{K}$

$\text{LN}_2 \sim 77\text{K}$

* $\begin{cases} \text{Tl}_2\text{Ca} & \text{Ba}_2\text{CuO}_9 \\ \text{Bi}_2\text{Ca} & \text{Sr}_2\text{Cu}_2\text{O}_9 \end{cases}$ $T_c \sim 80-125\text{K}$

$H_{c1} \sim 10\text{Oe}$

$H_{c2} \sim 100\text{T}$

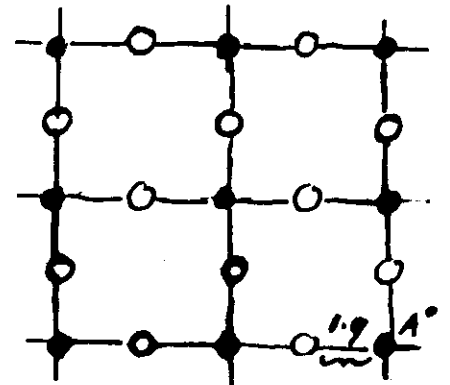
$H_c \sim 10^2\text{Oe}$

$H_{c2} \sim 10\text{T}$

* 'Chemical' SUPERCONDUCTORS
Ceramic Oxides, stoichiometry important.

Band Met Intermetallics

Also $\begin{cases} \text{BaPb}_{1-x}\text{BiO}_3, T_c \sim 12\text{K} \\ \text{K}_{1-x}\text{Ba}_x\text{BiO}_3, T_c \sim 30\text{K} \end{cases}$



CuO_2 planes
⊥ c-axis separated
by $\sim 6\text{\AA}$

La_2CuO_4 Tetragonal
Layered Perovskite
structure (K_2NiF_4)

Main Electronic
feature: square
planar CuO_2 layers

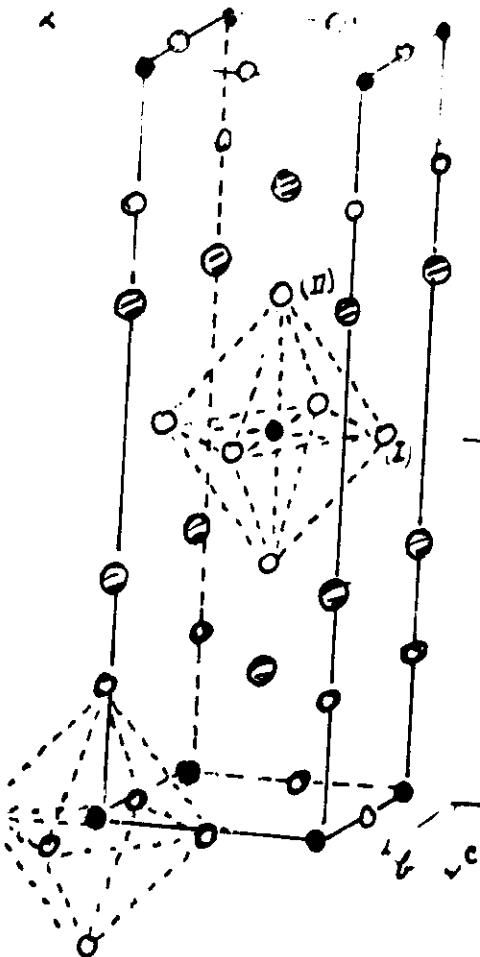
$\text{Cu-O(I)}: 1.9\text{\AA}$

$\text{Cu-O(II)}: 2.4\text{\AA}$

Weak inter-layer
coupling

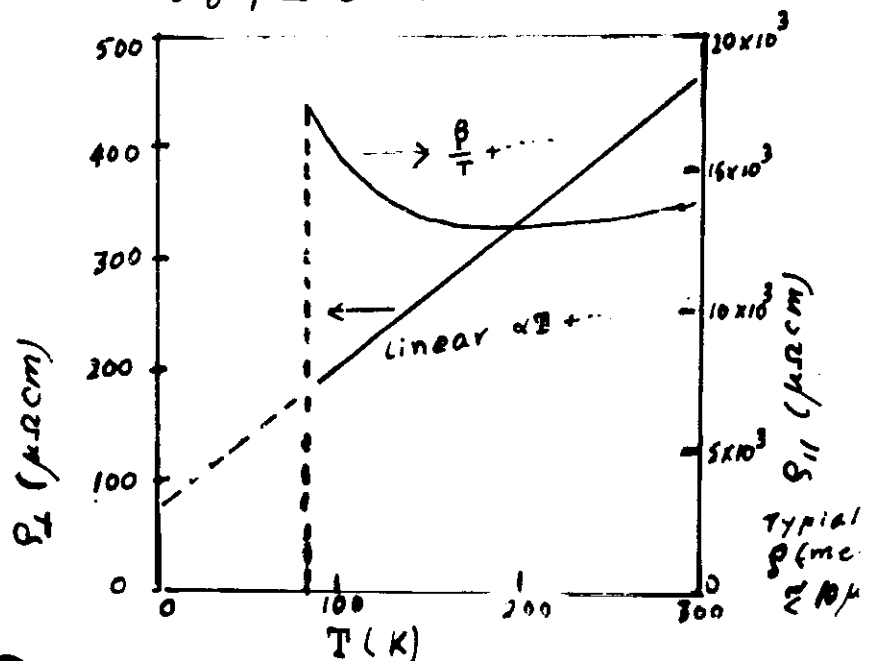
ANISOTROPIC
Layered (low dimensional)

La_2CuO_4 undoped - Insulator
a conductivity gap 2-3 eV.



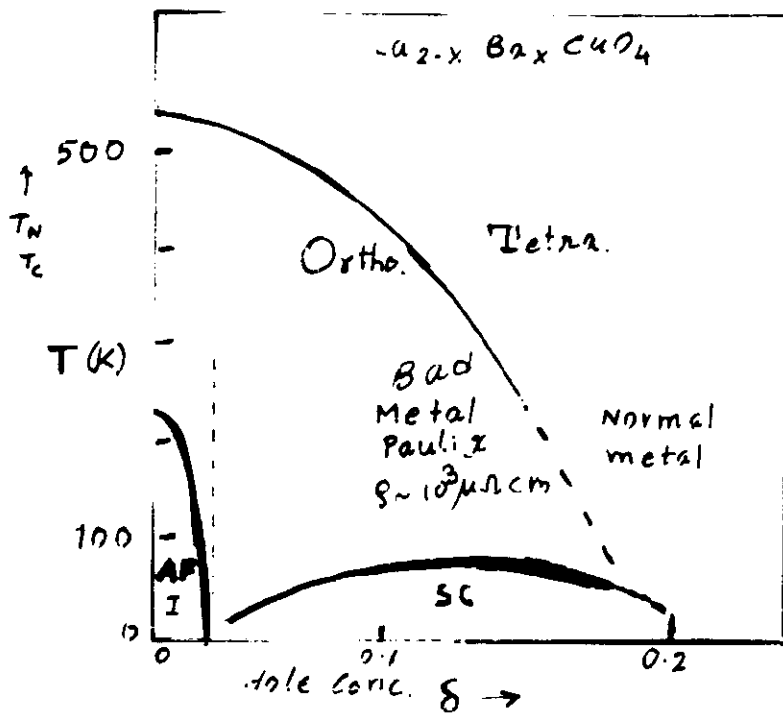
● La^{3+} $a = 3.78\text{\AA}$
● Cu^{2+} $b = a$
○ O^{2-} $c = 13.25\text{\AA}$

$\text{Cu}^{2+} = 3d^9$: half-filled
band should be a
band metal. But
actually an MF ($s = \frac{1}{2}$)
insulator (pure)
same for $\text{YBa}_2\text{Cu}_3\text{O}_{7-\delta}$

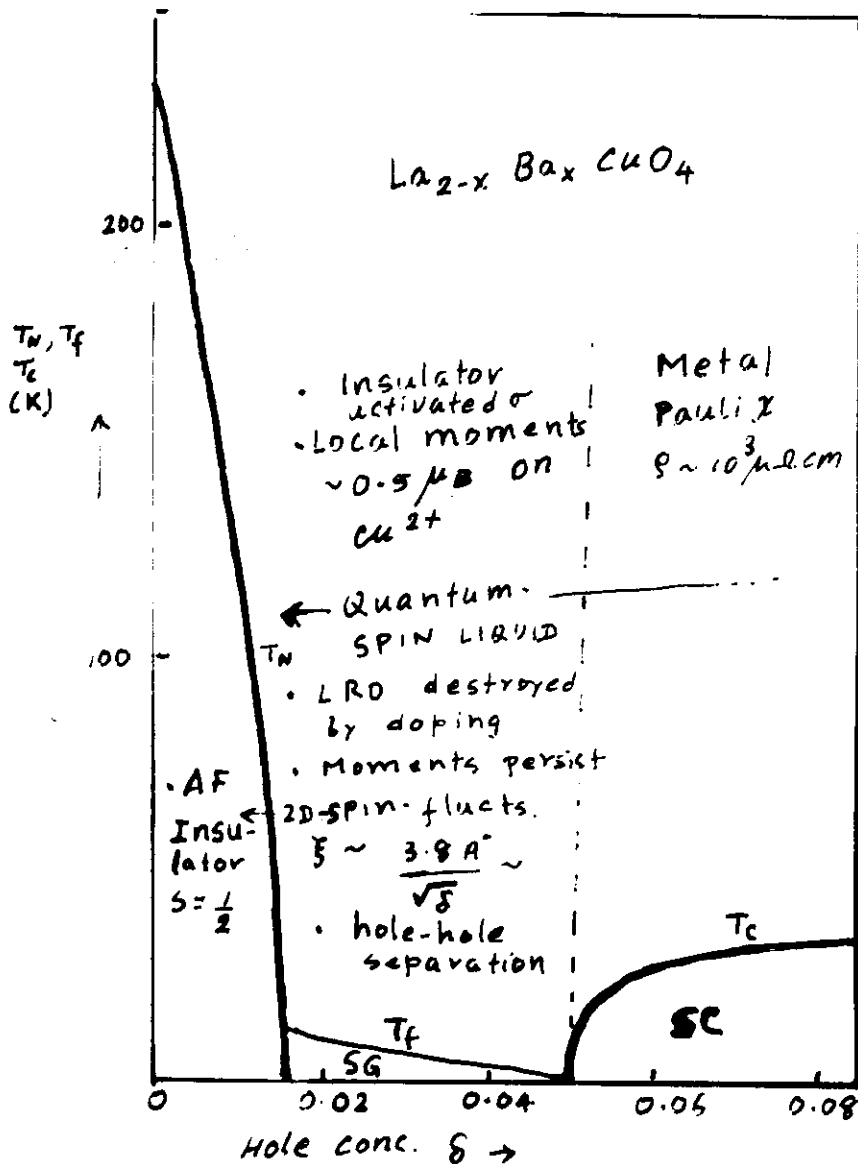


single crystal $\text{YBa}_2\text{Cu}_3\text{O}_{7-x}$

NEUTRON SCATTERING



- Pure La_2CuO_4 : AF ($T_N \sim 200$)
- $T > T_N$ Cu^{2+} : $S = \frac{1}{2}$, $0.5 \mu_B$
Primarily 2D spin-spin correlation $\xi \sim 200$
- At $T = T_N$ 3D ordering set
- $T(0)$ transition $\sim 550 \text{ K}$
- Both T_N , $T(T/0) \downarrow$ with $\delta \uparrow$
- AF order lost for $\delta > 0.03 < \text{percolation threshold}$.



- spin-spin corr. length $\xi \downarrow$ to $\sim 10 \text{ \AA}$ as $\delta \uparrow$ for $T > T_N$
- spins fluctuate rapidly $\tau_{SF} \sim 10^{-14} \text{ s}$ for $T > T_N$ (totally dynamic $S(q, \omega)$)

AF $\rightarrow$ SPINGLASS $\rightarrow$ SC
Insul. Insul.
as $\delta \uparrow$

Thus unlike $S \geq 1$ systems (e.g. La_2NiO_4 , La_2MnO_4) we have truly 2D - Quantum spin liquid and AF ordering is driven by the third dimensionality.

HIGH-TEMPERATURE SUPERCONDUCTIVITY

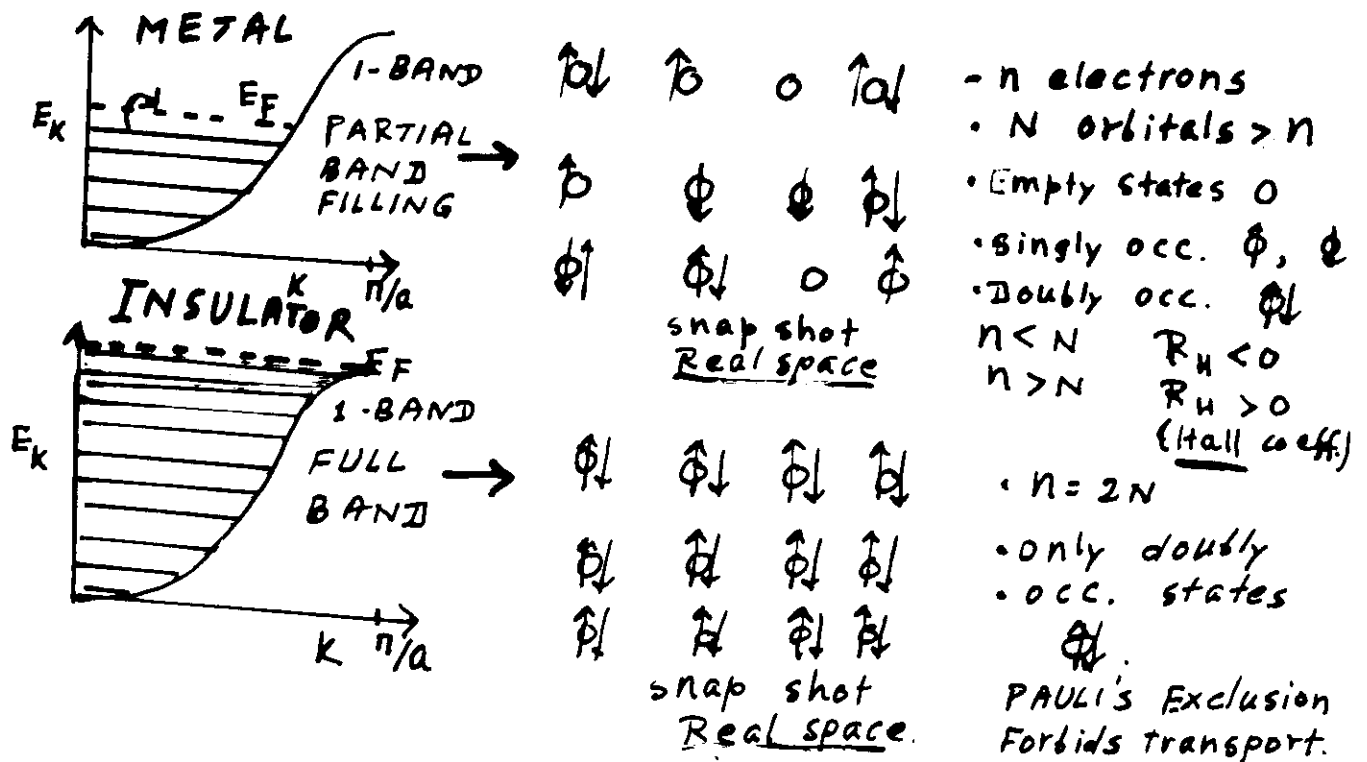
IN CERAMIC OXIDES: DEVIATION FROM INSULATING STATE

F.2

rather than a band-metallic state.

Why?

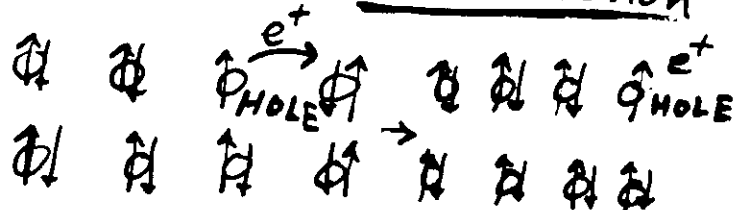
- WHAT MAKETH A METAL → BAND theory:
PARTIALLY FILLED BAND ⇒ Empty states
infinitesimally close to Fermi level ⇒ NO
GAP for CHARGE EXCITATION, hence conducts without
 activation.
- WHAT MAKETH AN INSULATOR → BAND theory:
FILLED BAND ⇒ FERMI LEVEL in the gap ⇒
CHARGE EXCITATION GAP, hence activated
 conduction.



- DOPING BAND INSULATOR → Semiconduction

Example:

1 hole ⇒



Hole : e^+ , spin $\frac{1}{2}$ Fermion ⇒ $R_H > 0$

* La_2CuO_4 : Parent compound (of $\text{La}_{2-x}\text{Sr}_x\text{CuO}_4$) has
BAND THEORY $\frac{1}{2}$ -filled "conduction band" SHOULD
FAILS → Cu be metal a la BAND THEORY BUT IS "2"

LaCuO_4 : is not a band insulator.
 is insulator because of
 strong electron-electron repulsion
 (on-site repulsion U) disfavouring
double occupancy $\Rightarrow$ singly-occupied
orbitals - only at $\frac{1}{2}$ -filling ($n=N$).
 Any charge transport involves
 double occupancy $\Rightarrow$ Coulomb gap $\sim U$.
 $\therefore$ Insulator (Mott-Hubbard Insulator)
 $\rightarrow$ STRONGLY CORRELATED FERMIONS

- COMPETITION between lowering of kinetic energy by delocalization ($\sim \frac{1}{2}$ Bandwidth) and of potential energy (U) by localization determines the physics of normal & SC states.
- Deviation from $\frac{1}{2}$ -filling $\Rightarrow$ itinerant charge carriers (different from doped band semiconductors)
- Strong Correlation (on-site repulsion U)
 - $\rightarrow$ Insulator at $\frac{1}{2}$ -filling
 - $\rightarrow$ Antiferromagnetism at $\frac{1}{2}$ -filling?
- Deviation from $\frac{1}{2}$ filling (by doping δ , $\text{La}^{3+} \rightleftharpoons \text{Ba}^{2+}$, or oxygen deficiency)
 - $\rightarrow$ destroys AF order quickly for small δ
 - $\rightarrow$ conduction in normal state (Anomalous)
 - $\rightarrow$ SC at low temp. & higher δ .

Seems that:

- We are dealing with strongly correlated, almost localized lattice bound fermions $\Rightarrow$ The charge- and spin- degrees of freedom may get dissociated leading to unconventional superconductivity - RVB
- Normal state properties reflect the unconventional SC.

Non-Fermi
Liquid behaviour:

Absence of
Fermi Surface.

Anderson (1987)

(4)

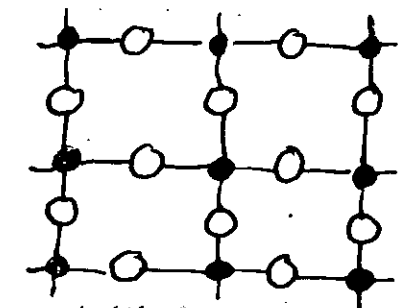
ELECTRONIC STRUCTURE → HUBBARD MODEL (2D) P.5

For La_2CuO_4

- Crystal structure (x-ray, neutrons)
- Anisotropy $\sigma_{||}/\sigma_{\perp} \sim 10^2$ (electrical)
- Magnetic correlation and dispersion (inelastic neutron scattering)
- Dispersionless calculated band structure // c-axis

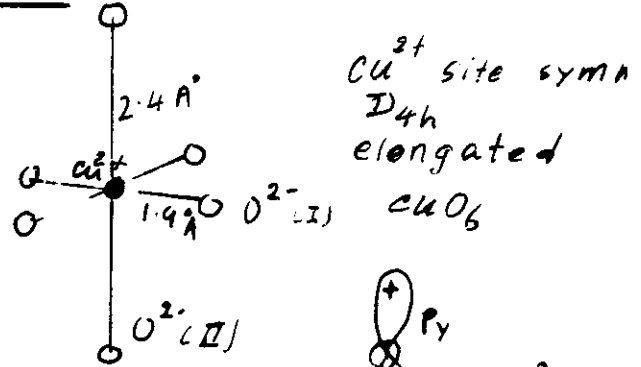


- Electronically 2D system of layers of corner-sharing elongated CuO_6 octahedra, layer separation $\sim 6 \text{ \AA}$
- Band Theory → metal. But actually Insulator → strong Correlation (like Ni)

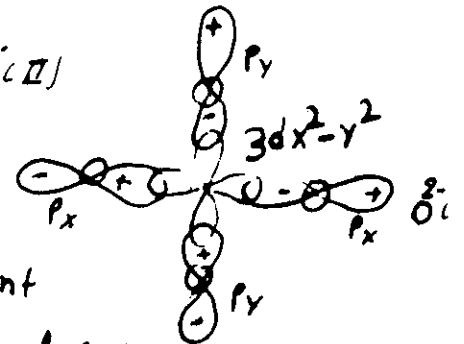


square planar CuO_2
local symm. at $\text{Cu}^{2+} : D_{4h}$

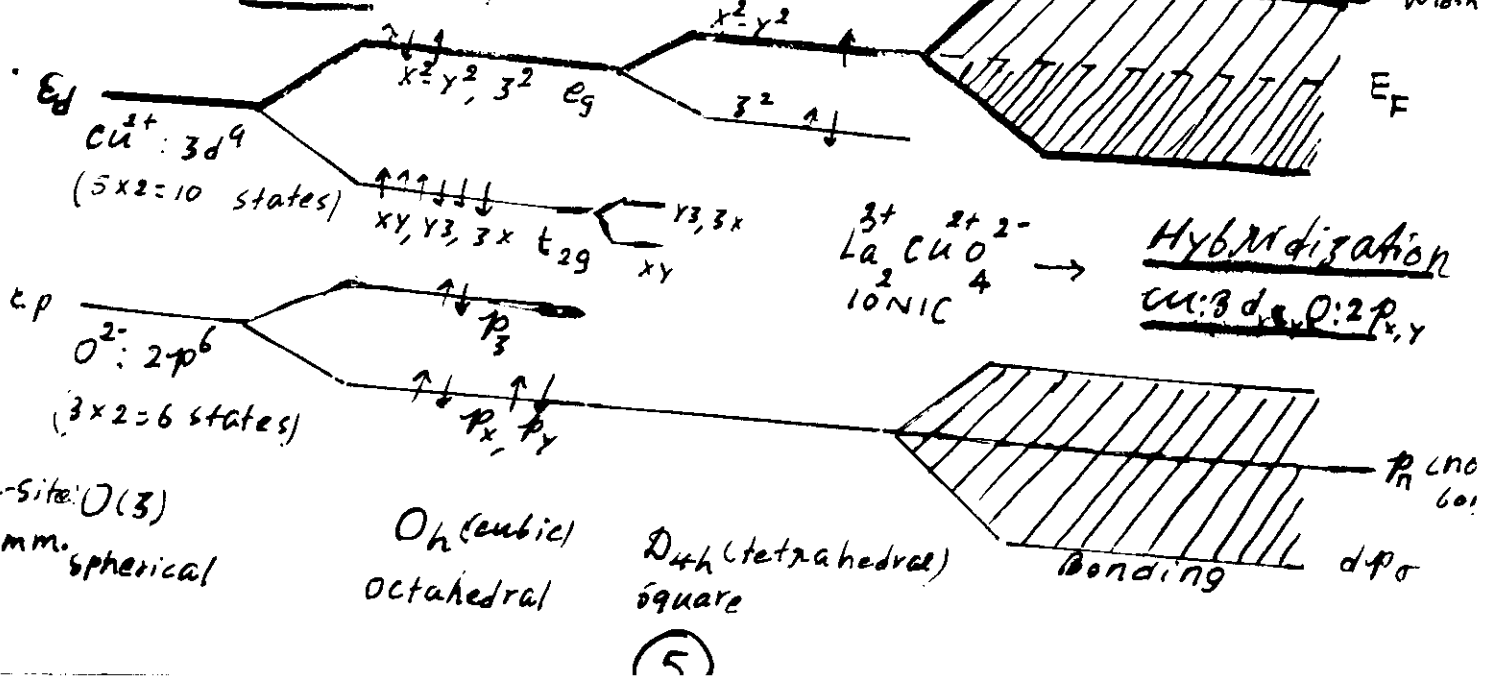
2D layers of CuO_2

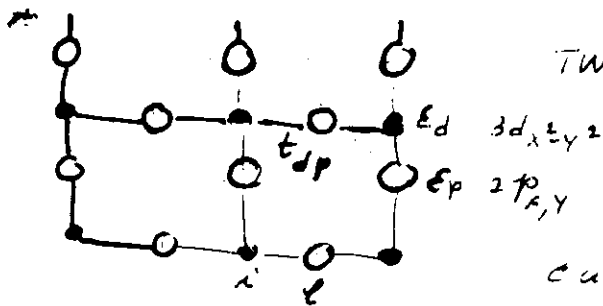


La_2CuO_4
 $3+2+2=2 \times 4$
- charge balance
Electron count



Energy Level Diagram
Essentially ionic crystal field splitting and stabilization by semicovalent hybridization with ligands (O^{2-})



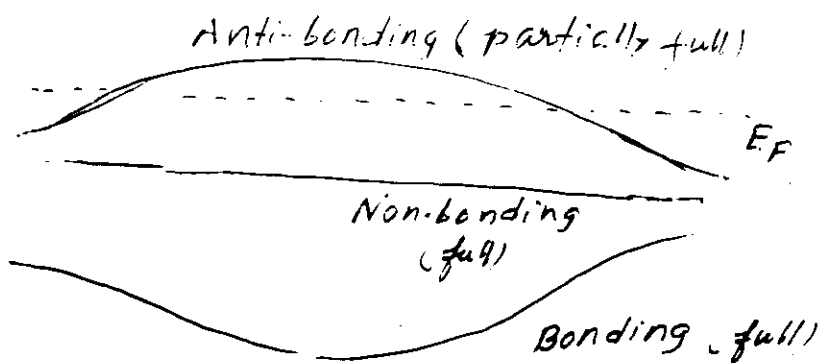


Two-band tight-binding Hamiltonian:

$$\sum_{i \in \text{Cu}} \epsilon_d d_i^\dagger d_i + \sum_{i \in \text{O}} \epsilon_p p_i^\dagger p_i + t_{dp} \sum_i (d_i^\dagger p_{i+1} + \text{h.c.})$$

can be diagonalized to give, non-bonding bonding and Antibonding bands.

$$\epsilon_k \pm \begin{matrix} \text{Anti-bonding} \\ \text{Bonding} \\ \text{Non-bonding} \end{matrix} = \left(\frac{\epsilon_d + \epsilon_p}{2} \right) \pm \frac{1}{2} \sqrt{(\epsilon_d - \epsilon_p)^2 + 8 t_{dp}^2 (1 + \cos k_x a + \cos k_y a)}$$



For $\epsilon_d - \epsilon_p \equiv \Delta \gg t_{dp}$, the high lying, partially full Anti-bond. band is well isolated, and is physically relevant.

this band can now be approximated by a one-band tight-binding Hamiltonian

$$H_0 = -t \sum_{\langle i,j \rangle} c_{i\sigma}^\dagger c_{j\sigma}$$

Here $|\phi_i\rangle$ effective Wannier orbital for the lattice cell i .

Now we can introduce the intra-orbital Coulomb repulsion $U \equiv$ cost of double occupancy.

$$H \equiv H_0 + H_2 = -t \sum_{\langle i,j \rangle} c_{i\sigma}^\dagger c_{j\sigma} + U \sum_i n_{i\uparrow} n_{i\downarrow} \quad \text{Hubbard Hamiltonian}$$

this is valid if $U \ll \Delta$ (Ignore Configurational Interaction)

* One-Band Hubbard Model in $D=2$
for strongly-correlated Electrons (tight-binding)

$$H = -t \sum_{\langle i,j \rangle} \sum_{\sigma} c_{i\sigma}^{\dagger} c_{j\sigma} + U \sum_i n_{i\uparrow} n_{i\downarrow}, \quad n_{i\uparrow} = c_{i\uparrow}^{\dagger} c_{i\uparrow}, \quad n_{i\downarrow} = c_{i\downarrow}^{\dagger} c_{i\downarrow}$$

t : transfer nn matrix element $\sim 1 \text{ eV}$, $W = 23t$ band width

U : Intra-orbital coulomb repulsion $\sim 10 \text{ eV}$ ($\text{Cu}^{2+} + \text{Cu}^{2+} \xrightarrow{U} \text{Cu}^{3+} + \text{Cu}^{1+}$)
Ionization - Affinity

$t/U \ll 1$

i : labels the Wannier (atomic) orbital at site i , N : no. of sites

n : no. of electrons $\leq N$

$\delta = 1 - n/N < 1$ deviation from half-filling $\equiv$

no. of holes/site created by doping

($\text{La}^{3+} \rightarrow \text{Ba}^{2+}$) or oxygen deficiency

• This is the ^{simplest} Hamiltonian $\rightarrow$ describes narrow band transition metal oxides...

• Exactly solved for $D=1$ only

for: Ground State Energy

Elementary excitation spectrum

spin-spin correlation

Migdal discontinuity at E_F

• PHYSICS is determined by competition between

delocalization (t) lowering kinetic energy

localization (U) lowering potential energy by suppressing

double ($\uparrow\downarrow$) occupancy

and no. of holes (δ) the available free volume in the crowded condition

• control parameter appears to be ($t/U\delta$):

$t/U\delta > \beta$... Antiferromagnetism

$t/U\delta < \beta$... ferromagnetism

$\alpha < t/U\delta < \beta$... non-magnetic

for $t/U \ll 1$

$\delta \ll 1$

• For Half-filled case ($\delta=0$): Metal $\rightarrow$ Insulator

transition (continuous) as t/U decreases

below a critical value ~ 1 . For $\delta \neq 0$ always metallic
(may not be Fermi-Liquid)

Qualitative Picture:

at $\delta=0$ (Half-filled) snapshot occupancy

$t/U \rightarrow \infty$
(No corr.)

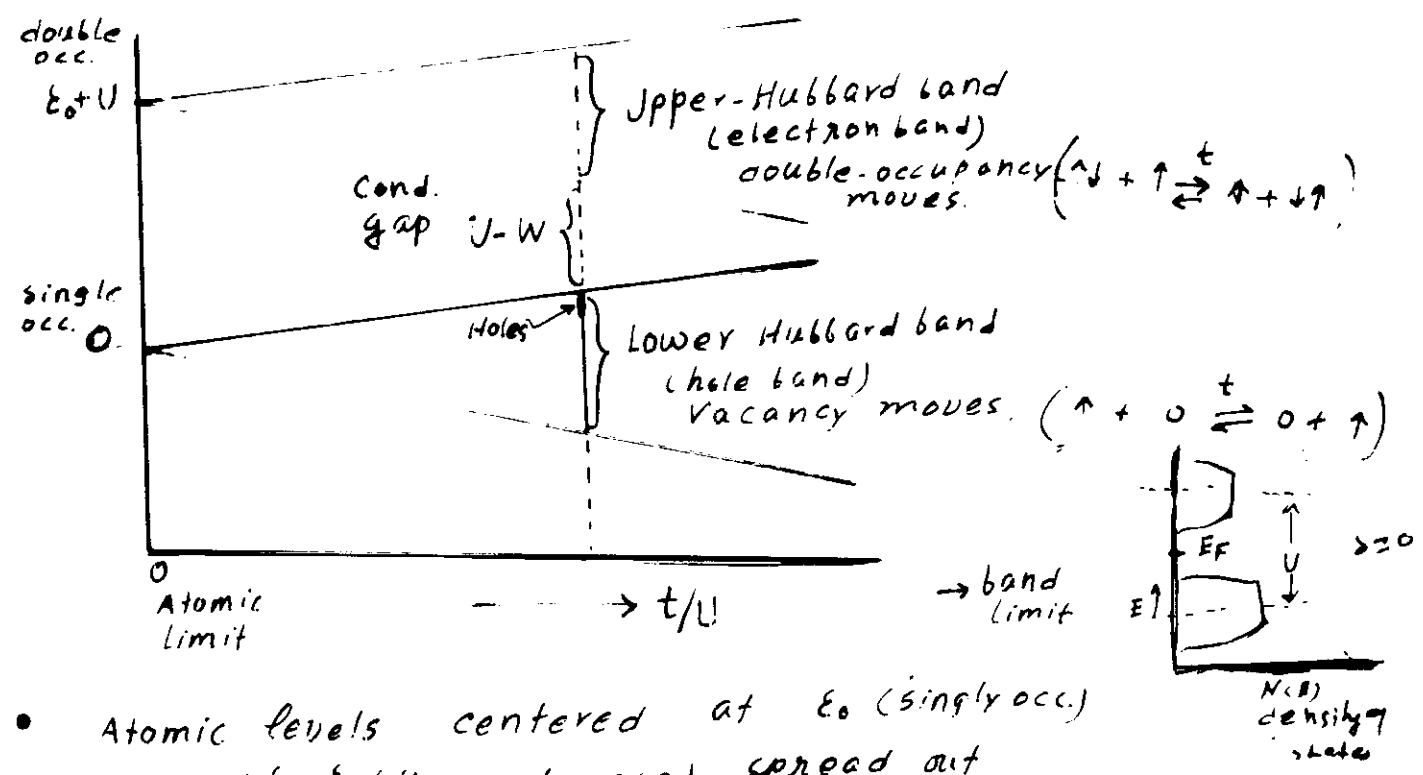
$\uparrow$	$\downarrow$	$\uparrow$	$\downarrow$	$\uparrow$	$\downarrow$	25% double occ.	} at random <u>Band</u> <u>Metal</u> <u>Pauli paramag.</u> doping ($\delta > 0$) just changes E_F
$\downarrow$	$\uparrow$	$\downarrow$	$\uparrow$	$\downarrow$	$\uparrow$	25% unocc.	
$\uparrow$	$\uparrow$	$\downarrow$	$\downarrow$	$\uparrow$	$\downarrow$	50% single occ.	
$\downarrow$	$\downarrow$	$\uparrow$	$\uparrow$	$\downarrow$	$\uparrow$		

$t/U \rightarrow 0$
(Strong corr.)

$\uparrow$	$\downarrow$	$\uparrow$	$\downarrow$	$\uparrow$	$\downarrow$	0% double occ.	} <u>Insulator</u> <u>Paramagne</u> doping ($\delta > 0$) → finite cond. & bc?
$\downarrow$	$\uparrow$	$\downarrow$	$\uparrow$	$\downarrow$	$\uparrow$	50% single occ. ($\uparrow$)	
$\uparrow$	$\uparrow$	$\downarrow$	$\downarrow$	$\uparrow$	$\downarrow$	50% " " ($\downarrow$)	
$\downarrow$	$\downarrow$	$\uparrow$	$\uparrow$	$\downarrow$	$\uparrow$		

suppresses double occ.
∴ No transport

Interpolation between two limits



- Atomic levels centered at E_0 (single occ.) and at E_0+U (double occ.) spread out into bands by hopping matrix element t centered at E_0 and E_0+U respectively. These are many-body bands, deceptively resemble a semiconductor picture.

* HUBBARD CORRELATION (U) on Copper : $Cu^{2+} + Cu^{2+} \rightleftharpoons Cu^{1+} + Cu^{3+}$
 CHARGE TRANSFER ENERGY Δ ; $Cu^{2+} + O^{2-} \rightleftharpoons Cu^{1+} + O^{2-}$
 BAND ENERGY (-t)

(Parameters U, Δ from Valence band photo emission, optical absorption, core-level shift)

- configurational Interaction (CI) Important

$U \ll \Delta$ Mott-Hubbard Insulator } for small t
 $U \gg \Delta$ CHARGE TRANSFER INSULATORS

In hole representation:

Let (hole vacuum) = $|Cu^{2+}, O^{2-}\rangle$
 $3d^9 \quad 2p^6$

$|Cu^{2+}, O^{2-}\rangle$ one hole on copper $\rightarrow$ Energy ... 0 (say) (undoped!)

$|Cu^{3+}, O^{2-}\rangle$... added hole also on copper $\rightarrow$ Energy ... $U_d \sim 5-10$ eV

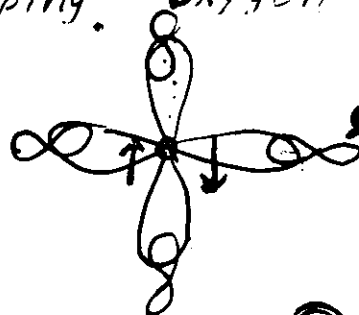
$|Cu^{2+}, O^{-}\rangle$ added hole on oxygen $\rightarrow$ Energy ... $\Delta \sim 2-4$ eV

• WHERE ARE THE HOLES : (No sign of Cu^{3+} in photoemission...)

The oxidation state of Cu^{2+} does not change

with doping. $\therefore$ Added holes go to oxygen (O^{-}), or O_2^{2-} hole_{on O^{-}} Exchange coupled to Cu^{2+} pre-existing hole $\rightarrow$ singlet.
 This moves like a hole in a one-band model.

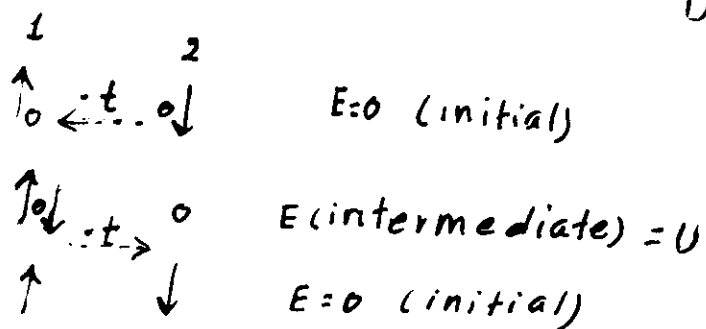
(The main feature: Interlacing of bands, No direct O-O hopping. Oxygen holes move via copper)



(a)

spin singlet (Cu^{2+}) hole-pair moves like a hole in one-band model. Internal structure of this singlet? A composite object.

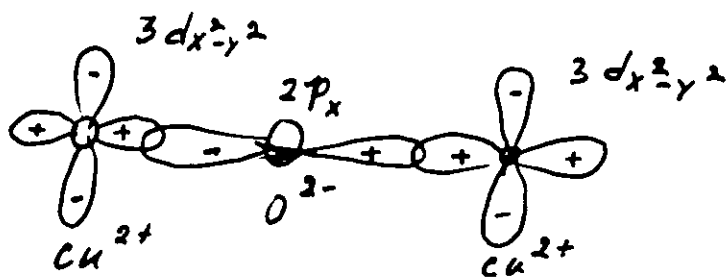
* [Note on Kinetic exchange $J = \frac{4t^2}{U}$ of Anderson.



This virtual process in which the orbital 2 is virtually doubly occupied (and the conjugate process in which orbital 1 is doubly occupied) lowers the energy of antiparallel state relative to parallel spin state by $2(-t)^2/U$. Antiferromagnetic

$$J(\hat{S}_1 \cdot \hat{S}_2 - \frac{1}{4}), J = \frac{4t^2}{U}$$

* For the actual system spins on Cu^{2+} bridged by diamagnetic O^{2-} , we have Super-exchange Antiferromagnetic



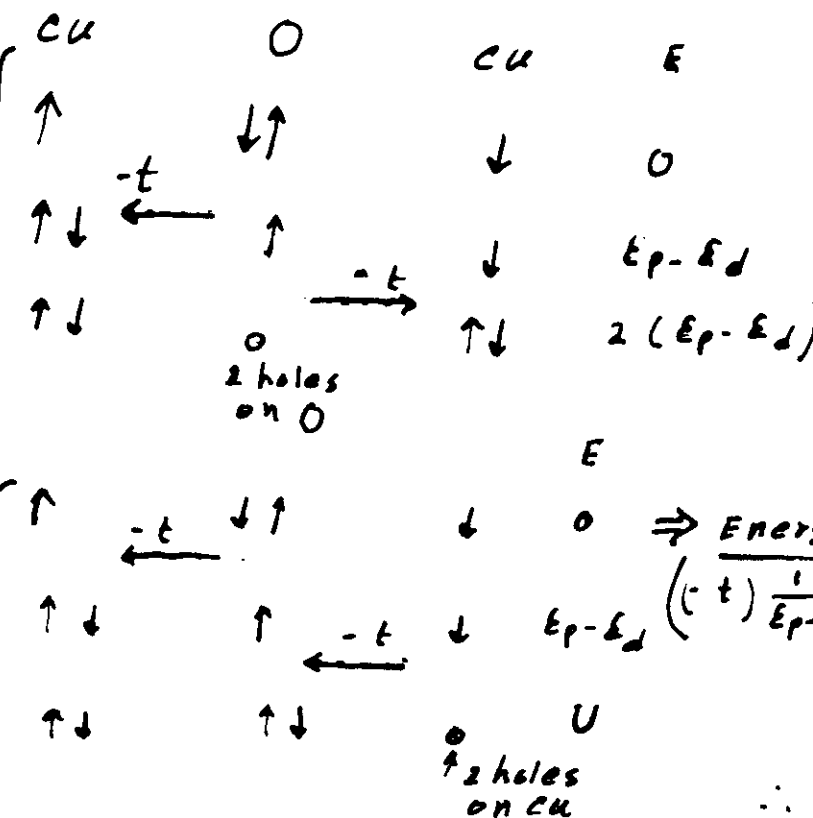
Hole representation:
 $|\text{Vacuum}\rangle \equiv |\text{Cu}^{1+}, \text{O}^{2-}\rangle$
 $|\text{Cu}^{3+}, \text{O}^{2-}\rangle \Rightarrow E = U + 1$
 $|\text{Cu}^{2+}, \text{O}^{2-}\rangle \Rightarrow E = 0, \text{sa.}$
 $|\text{Cu}^{1+}, \text{O}^-\rangle \Rightarrow E = E_p - E_d$

$\Rightarrow$ energy lowering

$$\left(\frac{-t}{E_p - E_d} \right)^2 \frac{1}{2(E_p - E_d)} = \frac{t^4}{2(E_p - E_d)^3}$$

superexchange

superexchange



$\Rightarrow$ Energy lowering:

$$\left(\frac{(-t)}{E_p - E_d} \right)^2 \frac{1}{U} = \frac{t^4}{(E_p - E_d)^2 U}$$

$$J = \frac{4t^4}{2(E_p - E_d)^3} + \frac{4t^4}{(E_p - E_d)^2 U}$$

Here On-site repulsion of holes on Cu is $U \sim 5-10 \text{ eV}$

1. BAND HUBBARD MODEL IN 2-DIMENSIONS AWAY FROM $\frac{1}{2}$ -FILLING (STRONG COUPLING LIMIT $U/t \gg 1$)

- n electrons and N sites (orbitals)
 $\delta = 1 - n/N$, deviation from $\frac{1}{2}$ filling (by doping, oxygen stoichiometry; $\delta > 0$, hole SC, $\delta < 0$, electron SC). Consider $\delta \gtrsim 0$.
- $H = -t \sum_{\langle ij \rangle} \sum_{\sigma} c_{i\sigma}^{\dagger} c_{j\sigma} + U \sum_i n_{i\uparrow} n_{i\downarrow}$
 U : on-site repulsion > 0
 $2zt$: Band width
 $t/U \ll 1$, disfavors double-occupancy
 $t \sim 1 \text{ eV}$, $U \sim 5-10 \text{ eV}$.
- For $t/U \ll 1$ good approximation to project out doubly occupied configurations
 Well known transformation $\rightarrow$ hole motion

$$\tilde{H} = -t \sum_{\langle ij \rangle} \sum_{\sigma} \underbrace{(1 - n_{i-\sigma}) c_{i\sigma}^{\dagger} c_{j\sigma} (1 - n_{j-\sigma})}_{\text{spin-dynamics}} +$$

$$+ \underbrace{\frac{4t^2}{U} \sum_{\langle ij \rangle} (S_i \cdot S_j - \frac{n_i n_j}{4})}_{J} + \dots$$
 (within sub-space of non-doubly occupied states).
 The constraint of non-double occupancy $\sum_{\sigma} n_{i\sigma} \leq 1$, approximately, reduces the effective band width, $t \rightarrow \delta t$. Then the control parameter is the ratio $J/\delta t \propto t/U$ that determines the nature of the ground state.
- For dimensionality ≥ 1 exact results not available.
 For $D=3$, the ground state is AF.

TWO scenarios suggested for ($t/U < 1$)

- 1. At $\frac{1}{2}$ -filling, $S=0 \Rightarrow$ AF (antiferromagnetic) ground state (Neél like ordering with large zero-point spin fluctuations $\therefore$ low-dimensionality ($D=2$) and low spin ($=\frac{1}{2}$). Added holes ($S \geq 0$) move in AF background and pairing of magnetic origin. SC due to condensation of these Bose-like compact pairs.
Simple minded.
Emery
Hirsch (1987)
Mohan & Kumar

- (2) At $\frac{1}{2}$ -filling (and aided by doping), the ground state is a Quantum SPIN Liquid $\rightarrow$ Resonating Valence Bond state (RVB) and doping is Solitonic, leading to Unconventional Superconductivity — originated by Anderson (1987) and extended by Princeton group Baskaran, Zou and Santa Barbara Group Kivelson ...
This is the most extensively and intensively studied mechanism
Many others.

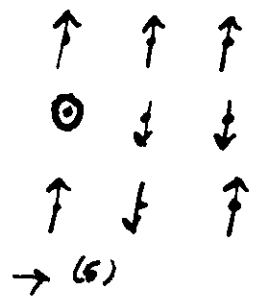
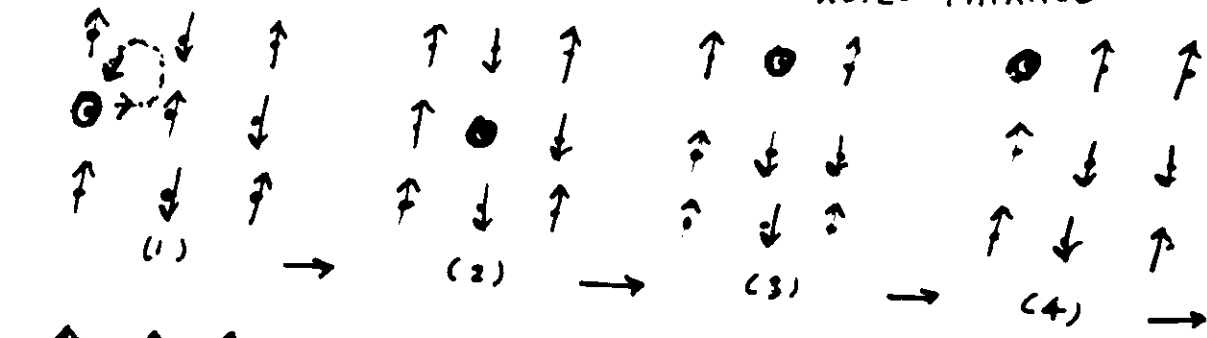
- Numerical simulations tend to support the non-fermi liquid behaviour.
But the ground state and the possibility of SC in 1-band Hubbard model still not conclusive.
• An elementary account follows.

BACKGROUND (Neel Like)

A

closed-loops

: Confining string & hole-PAIRING



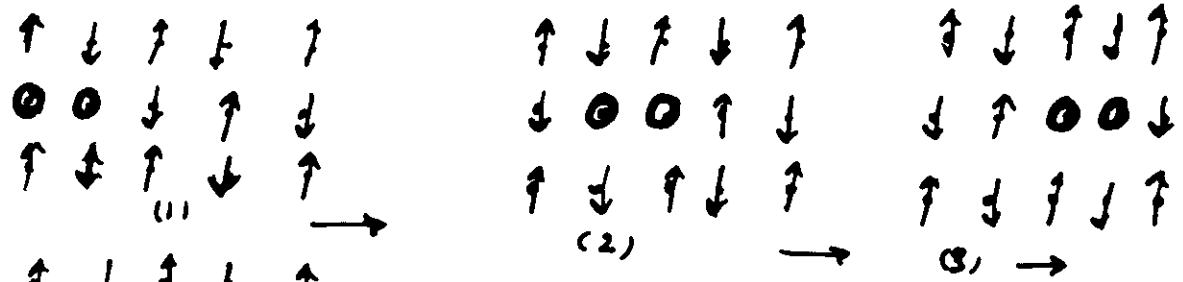
THUS (1) $\rightarrow$ (5) hole returns to original site on closed-loop but background changed $\Rightarrow$ description entirely in terms of hole position alone not possible. (Unwinding possible).

Ignore these closed-loop (higher order) motion

$\Rightarrow$ SELF-RETRACING PATH APPROXIMATION
 $\Rightarrow$ effectively Bethe Lattice topology.

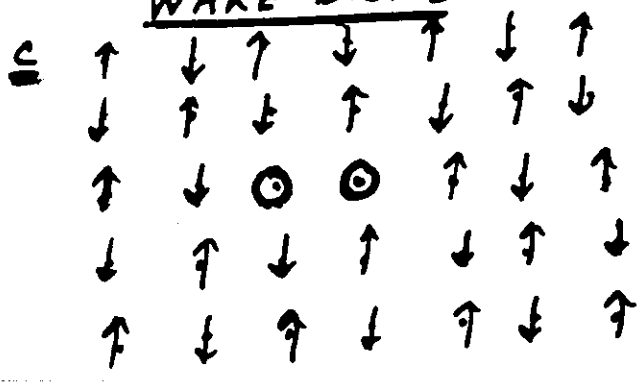
B

TWO Holes can Co-move without altering background:
 Motion of hole concomitant with spin flip = strong spin-hole coupling

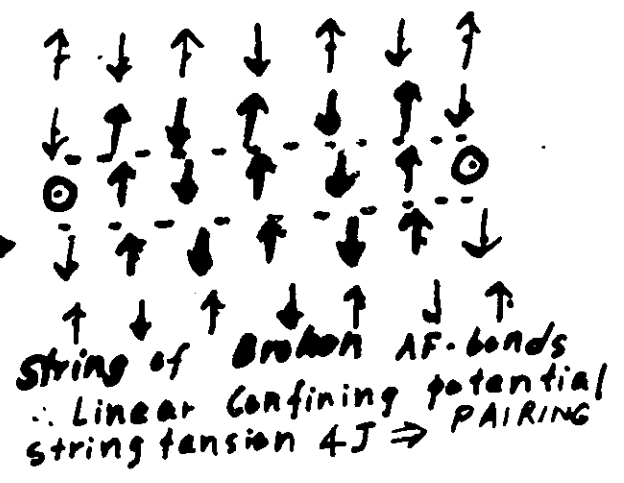


From (1) $\rightarrow$ (4) AF background is preserved. one hole undoes the second hole.

WAKE-BOUND HOLES



Holes moved Apart $\rightarrow$



(13)

Valence Bond & Resonating Valence Bond

P.14

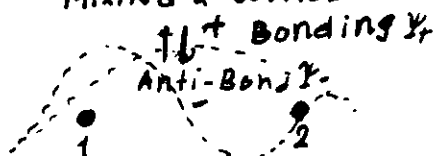
Chemical Bond:

- * Valence Bond (H_2): Two orbitals and 2 electrons (exactly solved simple case)

$$H = \epsilon_0 C_{1\sigma}^\dagger C_{1\sigma} + \epsilon_0 C_{2\sigma}^\dagger C_{2\sigma} - t(C_{1\sigma}^\dagger C_{2\sigma} + h.c.) + U n_{1\uparrow} n_{1\downarrow} + U n_{2\uparrow} n_{2\downarrow}$$

- Molecular Orbital : $t/U \gg 1$ Weak coupling

MIXING & COVALENCE

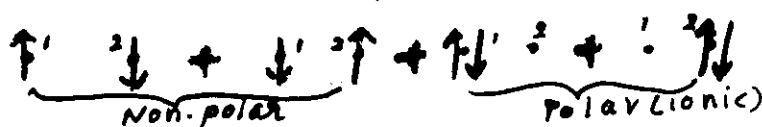


→ Ground state $\equiv C_{+\uparrow}^\dagger C_{+\downarrow}^\dagger |0\rangle$ → Linear comb. of polar and covalent conf. → Met. limit
Singlet (Bond. state occ. Anti-bond. empty)

$$\psi_{\pm} = (|1\rangle \pm |2\rangle) / \sqrt{2}$$

$$C_{\pm\sigma}^\dagger = (C_{1\sigma}^\dagger \pm C_{2\sigma}^\dagger) / \sqrt{2}$$

(one-electron states)



- Heitler-London Exchange : $t/U \ll 1$, strong Coupling

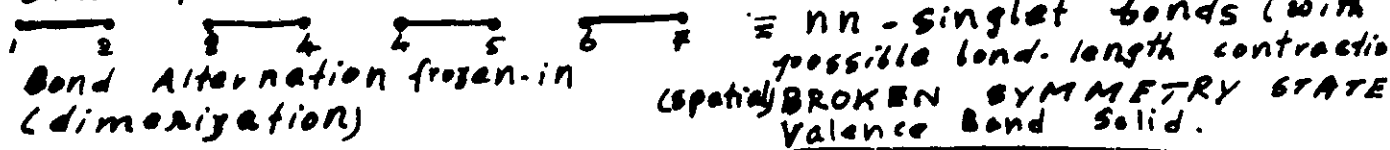
Singlet state without double occupancy

$$\frac{1}{\sqrt{2}} (C_{1\uparrow}^\dagger C_{2\downarrow}^\dagger - C_{1\downarrow}^\dagger C_{2\uparrow}^\dagger) |0\rangle \rightarrow \uparrow \downarrow + \downarrow \uparrow \rightarrow \text{Atom. limit}$$

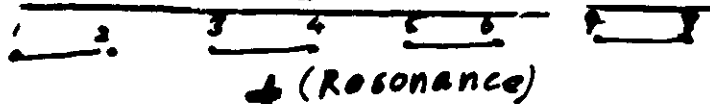
NO ionic config.

- * Extended System ($t/U \ll 1$) : {singlet bond $(|1\uparrow\downarrow\rangle - |1\downarrow\uparrow\rangle) / \sqrt{2}$ } denoted by $\equiv$

- SPIN-PEIERLS state (Jahn-Teller)

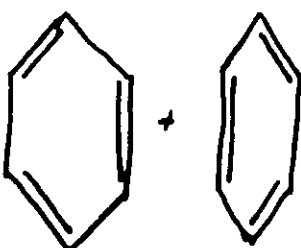


- RESONATING VALENCE BOND



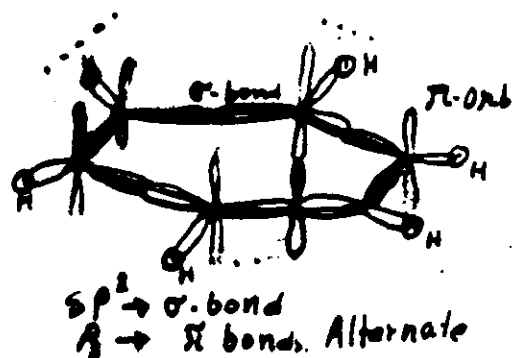
No dimerization, no spatial broken symmetry.

TWO degenerate bond alternation patterns and hence quantum resonance (of valence bonds).



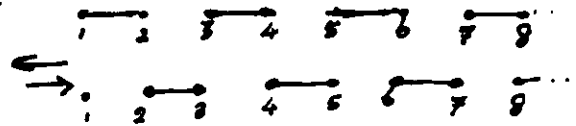
Resonance: single- and double-bond alternation patterns resonate

Benzene Ring, other aromatic and conjugated annulenes.

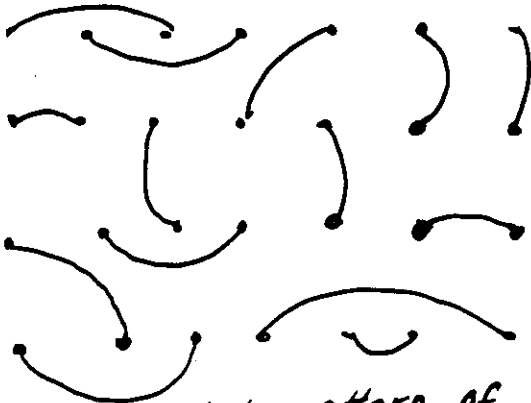
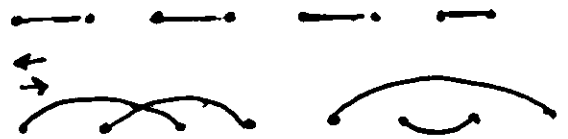


$$z_{\text{in } D} = 1$$

- Nearest Neighbour (nn) Bonds
Can resonate only synchronously
 $\therefore$ obstruction to resonance.



- Free asynchronous resonance
requires larger range or/and
higher dimensionality



A snapshot pattern of singlet bonds in 2D.



Asynchronous resonance with nn bonds in 2D
(Not orthogonal!)

- An RVB state is a coherent superposition of all possible patterns of singlet (dimer) covering of the lattice. The constraint of non-double occupancy and the singlet spin multiplicity gives RVB state a topological structure. Overcomplete
- The RVB ground state is : Spin Singlet
as we shall see
without spatial symm. breaking
(Featureless). Incompressible.
Quantum spin liquid (QSL)
with gapless spin (covalent) excitations
but charge (ionic) excitations have gap - RVB INSULATOR.

SPINONS → • Pseudo Fermi surface
• Linear-Temp. Sp. heat at low temp. in normal and SC state
• Pauli like χ

Holons → • Bose condensation → SC at low doping

→ • Linear $\rho-T$:: holon spinon scattering

→ • Tunneling

• can be made conducting by doping (removing electron) → 'holes' moving in background of non-doubly occ. sites

• Topological excitations →
• holons (+ve charge spinless hard core bosons)
• spinons (spin $\frac{1}{2}$ neutral fermions but have magnetic moment).

• • • • • τ • • • • • singlet valence bond τ :

• • • • • $b_{\tau}^{\dagger} |0\rangle = \frac{1}{\sqrt{2N}} \sum_{i,j} (C_{i\uparrow}^{\dagger} C_{i+\tau\downarrow}^{\dagger} - C_{i\downarrow}^{\dagger} C_{i+\tau\uparrow}^{\dagger}) |0\rangle$

• • • • • $\uparrow$ creates bond

"Cooper Pair" Wavefunction

General bond with bond-length distribution of weight $|a_{\tau}|^2 \rightarrow b^{\dagger} = \sum_{\tau} a_{\tau} b_{\tau}^{\dagger} = \sum_{\underline{k}} a(\underline{k}) C_{\underline{k}\uparrow}^{\dagger} C_{-\underline{k}\downarrow}^{\dagger}$

• constraint of no double occupancy ($a_{\tau=0}=0$) $\Rightarrow \sum_{\underline{k}} a(\underline{k}) = 0$

[Anomalous $\langle b \rangle \neq 0$, suppressed by phase-fluctuation for $\delta=0$]

• To construct an RVB state for N electrons and N latticesites ($S=0$):

(i) prepare a singlet pair in zero momentum state $\dots \left(\sum_{\tau} a_{\tau} b_{\tau}^{\dagger} \right) |0\rangle$

(ii) prepare $N/2$ singlet pairs $\dots \left(\sum_{\tau} a_{\tau} b_{\tau}^{\dagger} \right)^{N/2} |0\rangle$

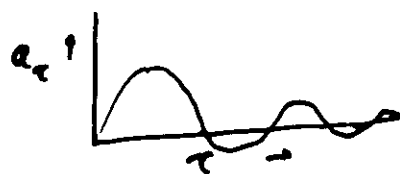
$= \left(\sum_{\underline{k}} a_{\underline{k}} C_{\underline{k}\uparrow}^{\dagger} C_{-\underline{k}\downarrow}^{\dagger} \right)^{N/2} |0\rangle$

(iii) Project out states with double occupancy $\prod_i (1 - n_{i\uparrow} n_{i\downarrow}) \left(\sum_{\tau} a_{\tau} b_{\tau}^{\dagger} \right)^{N/2} |0\rangle$

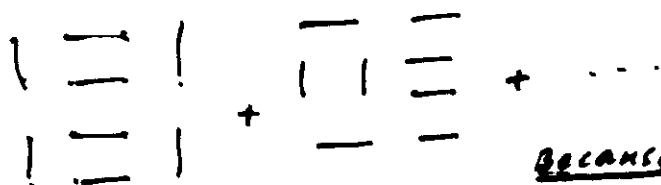
$\uparrow$ Take Jastrow corr. factor

$\equiv P_D \left(\sum_{\underline{k}} a_{\underline{k}} C_{\underline{k}\uparrow}^{\dagger} C_{-\underline{k}\downarrow}^{\dagger} \right)^{N/2} |0\rangle$

Range of a_{τ} determines the nature of RVB :



Microcanonical BCS Wavefunction (incompressible) singlet valence pairs $\leftrightarrow$ Cooper pairs.



Because of 'short-range' lattice structure $\Rightarrow$

Possible symm. of Valence Bond (Cooper Pairs): $\Delta(\underline{k}) = \sum_{\tau} a_{\tau} e^{i \underline{k} \cdot \underline{\tau}}$

$\Delta(\underline{k}) = \Delta_0$ (constant) s-wave

$\Delta(\underline{k}) = \Delta_0 (\cos k_x a + \cos k_y a)$ Extended s-wave

$\Delta(\underline{k}) = \Delta_0 (\cos k_x a - \cos k_y a)$ d-wave

$\Delta(\underline{k}) = \Delta_0 [(\cos k_x a + \cos k_y a) + i(\cos k_x a - \cos k_y a)] \equiv \text{c + i d wave}$ } Anisotropic flux phase.

Note on Local Gauge Invariance & RVB

- At half-filling ($\delta=0$) the Hamiltonian

$$\tilde{H} \approx -st \sum_{\langle i,j \rangle} c_{i\sigma}^\dagger c_{j\sigma} + \frac{4t^2}{U} \sum_{\langle i,j \rangle} (s_i s_j - \frac{n_i n_j}{4})$$

is invariant under site-dependent
(local) gauge

$$c_i \rightarrow e^{i\theta_i} c_i$$

and hence $\langle b_{ij} \rangle = \langle \frac{1}{\sqrt{2}} (c_{i\uparrow}^\dagger c_{j\downarrow} - c_{i\downarrow}^\dagger c_{j\uparrow}) \rangle = 0$
(unlike the global gauge symm, if the Hamiltonian has local gauge symm. then only gauge-invariant quantity can have non-zero average value $\equiv$ local gauge symm. can not be broken spontaneously - it is like a finite system).

- Away from $\frac{1}{2}$ -filling, $\delta \neq 0$, the first term destroys local gauge symm. Then the phase for the singlet can not be varied freely - it costs torsional energy $\sim \delta t (1 - \cos \theta) \sim \frac{\delta t \theta^2}{2}$

$$\langle b_{ij} \rangle \propto \langle b_{ij} \rangle_{T=0} \int e^{i\theta} e^{-\frac{\delta t \theta^2}{2k_B T}} d\theta \propto \langle b \rangle_{T=0} e^{-\frac{k_B T}{2\delta t}}$$

Here θ is the phase of b_{ij} relative to neighbouring pairs.

Thus the RVB order parameter assumes non-zero value below some temp. to be given by a self-consistent treatment of the Hamiltonian as in Gor'kov factorization.

This however, is not quite the SC order parameter.

SC is attributed to holons that move in this featureless singlet medium.

Thus RVB state is ^{mathematically} like BCS-paired state but projected so as to avoid double occupancy. For exact $\frac{1}{2}$ -filling, the 'incompressibility' destroys ODLRO. But doping provides the necessary free phase-space. One can think of SC resulting from these pre-existing singlet pairs (early version).

- Mean-field treatment proceeds via the anomalous expectations along the BCS line but there are important differences because of the constraint.
- The RVB theory is evolving continually with the identification of new internal symmetries.
- In the following, we consider some important aspects pictorially:

The new topological objects $\rightarrow$

Spinons

Holons

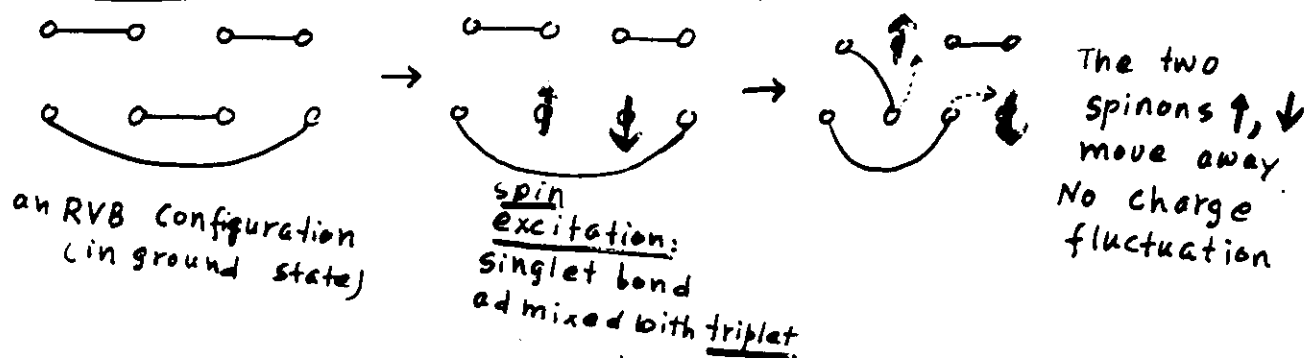
suggesting total separation of charge and spin-degrees of freedom.

Doped RVB Insulator vs. Doped Band Insulators

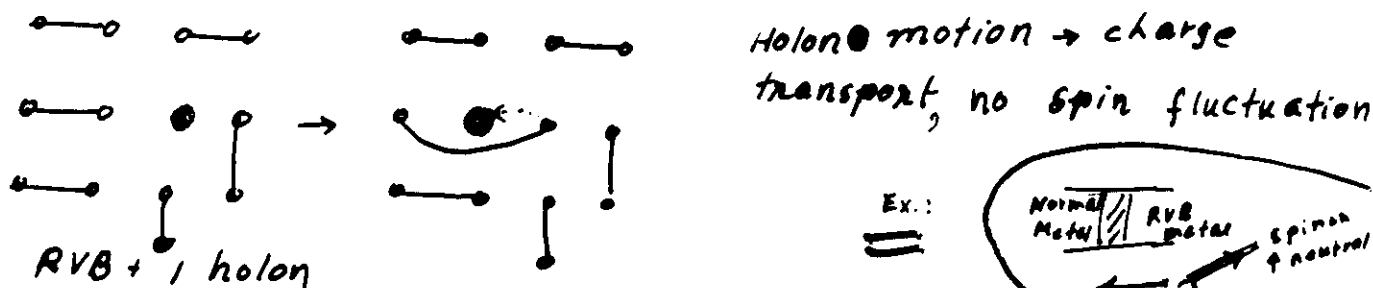
SPINONS & HOLONS

p.1

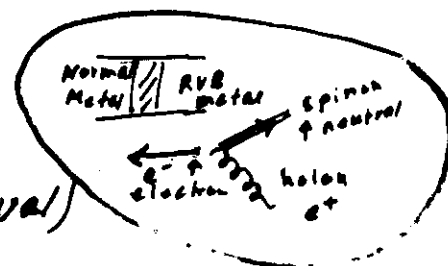
- SPINONS (Created in pairs): $s = \frac{1}{2}$, $q = 0$, mag. moment $\neq 0$



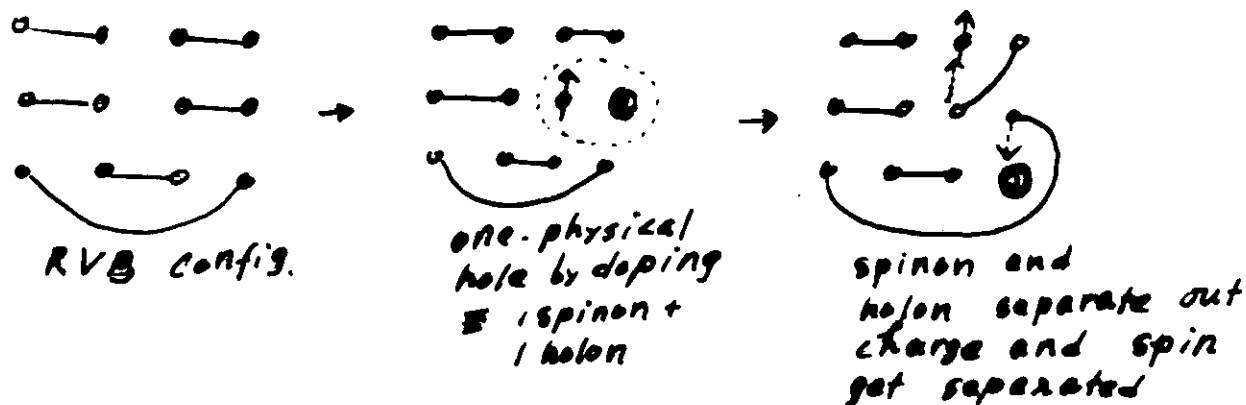
- Holons: $s = 0$, $q = |e|$, mag. moment $= 0$



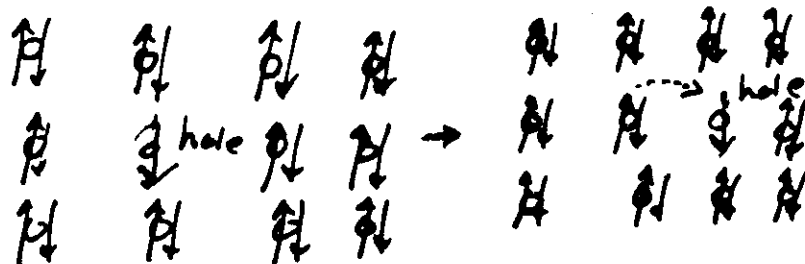
Ex.:



- PHYSICAL HOLE (DOPING = electron removal of RVB INSULATOR)



compare with:
DOPING OF BAND INSULATOR (removal of spin $\uparrow$ electron):
A hole moving in background of doubly occupied sites



Hole motion transports +ve charge and spin $\uparrow$.

RVB Order parameter:

P.19

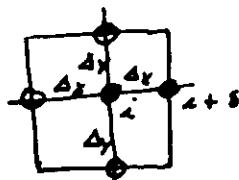
$$\langle S_{i\uparrow}^+ S_{j\downarrow}^- \rangle \equiv \Delta_{ij}$$

$$\Delta_y = e^{i\theta} \Delta_x$$

$\theta = 0 \Rightarrow$ s-wave

$\theta = \pi \Rightarrow$ d-wave

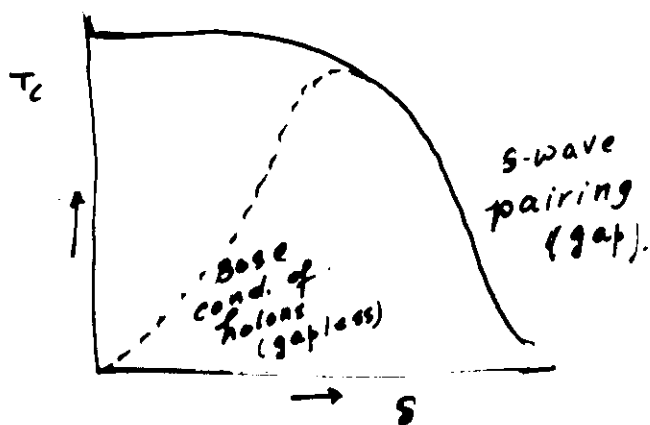
$\theta = \pi/2 \Rightarrow$ s+id-wave



lines of zero of gap will affect tunneling, NMR relaxation, sp. heat etc.

supercond. order parameter:

$$\langle c_{i\uparrow}^+ c_{j\downarrow}^+ \rangle \propto \langle S_{i\uparrow}^+ S_{j\downarrow}^+ \rangle \langle b_{i\downarrow} b_{j\downarrow} \rangle$$



Relative stability of s, d and s+id wave phases is very controversial (d-wave appear to be favoured)

these affect:
Recent Cu & oxygen NMR results should provide crucial test of these ideas

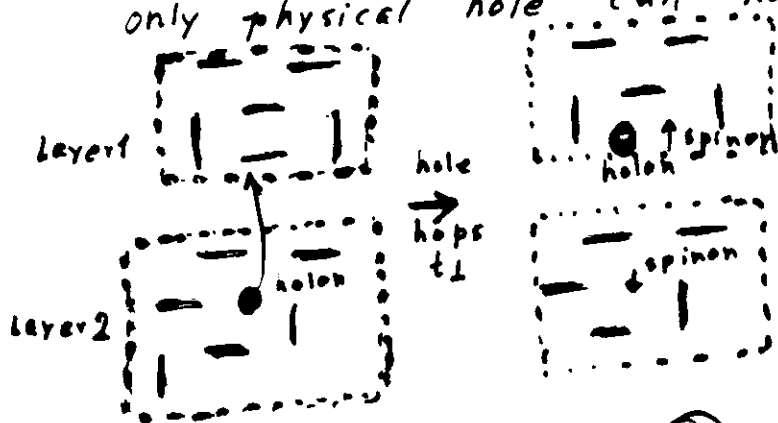
Tunneling N's ; s/s
sp. heat - linear
 T^{-1} NMR relaxation
 $\chi \sim$ Pauli like
 $\rho \sim$ temp. linear
Flux quantisation?
Andreev reflection?
light scattering (Raman)?

still?

Is RVB merely a matter of representation? overcomplete set.

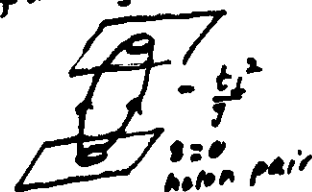
* Inter-layer holon-holon pairing (exchange of spinons):

only physical hole can hop interlayer (t_2):



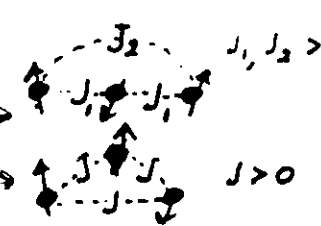
Thus inter layer hopping $\rightarrow$ two spinons (energy cost $\sim J$)
 $\therefore$ In second order $\Rightarrow$ holon-holon pairing

$$K T_c \sim t_2^2 / J$$



* What Stabilizes RVB state against AF Long Range Order r2

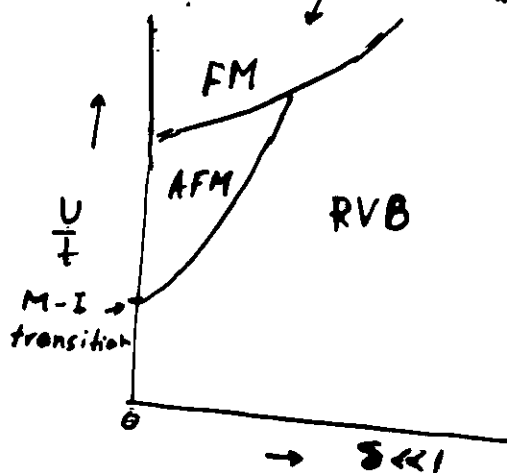
1. Low Dimensionality (D) : • 3D systems have AF ground state
• 2D systems are numerically found to be AF in thermodynamic limit
• 1D system has no LRO

2. Geometric Frustration : nn AF coupling $\rightarrow$  $J_1, J_2 > 0$
can not make all spins happy at the same time. Triangular lattice $\Rightarrow J > 0$

3. Low Spin (S)
 $S = \frac{1}{2}, \frac{1}{2}$ - integral $\rightarrow$ no spectral gap correlation decays algebraically
 $S = 1, \dots$ integral $\rightarrow$ spectral gap exponential decay
 $\text{La}_2\text{NiO}_4, \text{La}_2\text{MnO}_4, \text{La}_2\text{CoO}_4 \dots$ AF 3D $S=1$
 $\text{La}_2\text{CuO}_4 \dots$ essentially 2D spin fluids ordered by third dimension $S=\frac{1}{2}$

+ Doping S

Very Rough phase diagram



Doping stabilizes RVB?

destroys AF rapidly dynamically

Competition between:

Lowering of mobile hole energy due to delocalization ($\propto \delta t$)
cost of magnetic energy ($\propto \frac{J^2}{U}$) due to spin misalignment

Finally, a Remark : It appears that for valence bonds to resonate in an extended solid, there should be a back-bone structure that holds the solid together on its own more or less. Otherwise resonance may be blocked by spatial broken symmetry.